

# UT2309

**Power MOSFET**

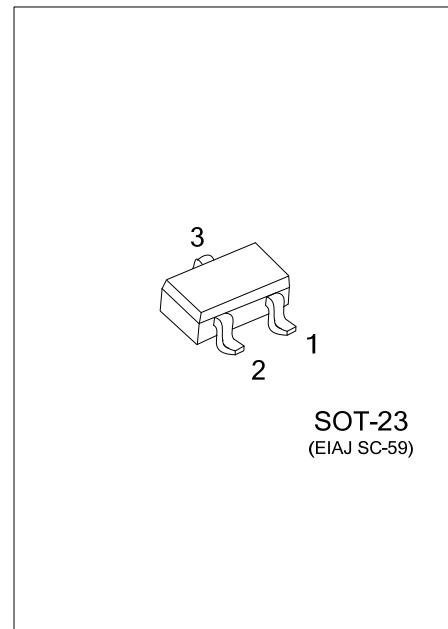
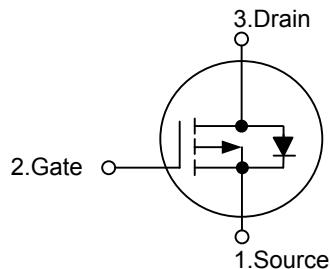
## P-CHANNEL ENHANCEMENT MODE

### ■ DESCRIPTION

The **UT2309** is P-channel power MOSFET, designed with high density cell with fast switching speed, ultra low on-resistance and excellent thermal and electrical capabilities.

Used in commercial and industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

### ■ SYMBOL



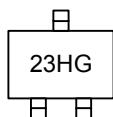
### ■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
UT2309G-AE3-R	SOT-23	S	G	D	Tape Reel

Note: Pin Assignment: S: Source G: Gate D: Drain

UT2309G-AE3-R	(1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free and Lead Free
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### ■ MARKING



### ■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DSS}$	-30	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 3)	$I_D$	-3.7	A
Pulsed Drain Current (Note 1, 2)	$I_{DM}$	-12	A
Total Power Dissipation	$P_D$	1.38	W
Junction Temperature	$T_J$	+150	°C
Storage Temperature	$T_{STG}$	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.  
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

### ■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient (Note 3)	$\theta_{JA}$	90	°C/W

### ■ ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ C$ , unless otherwise specified)

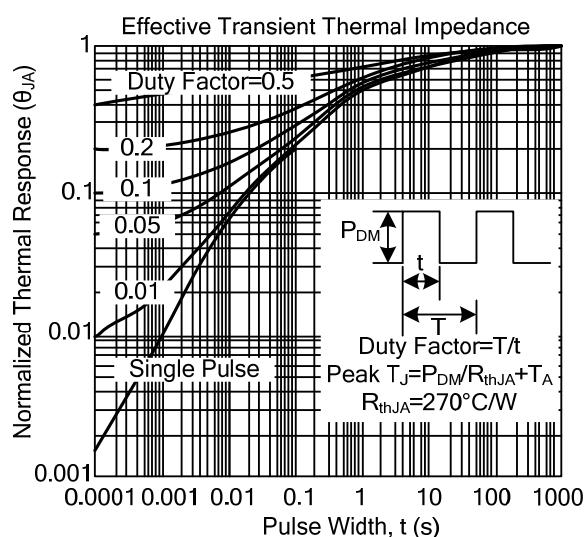
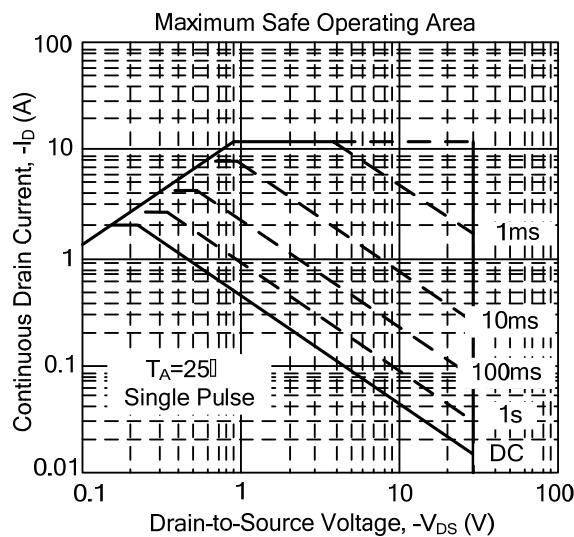
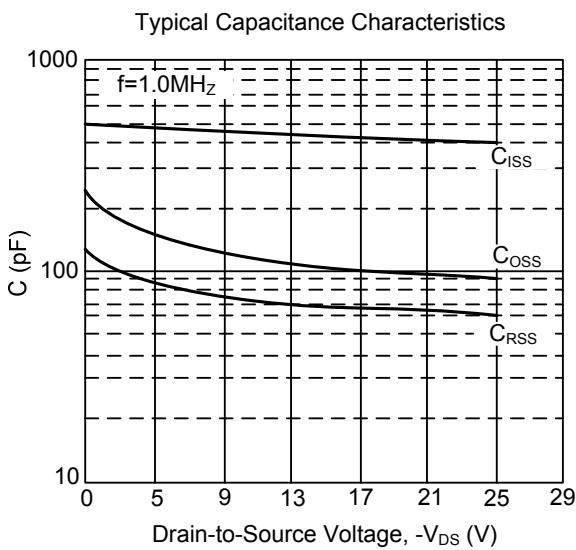
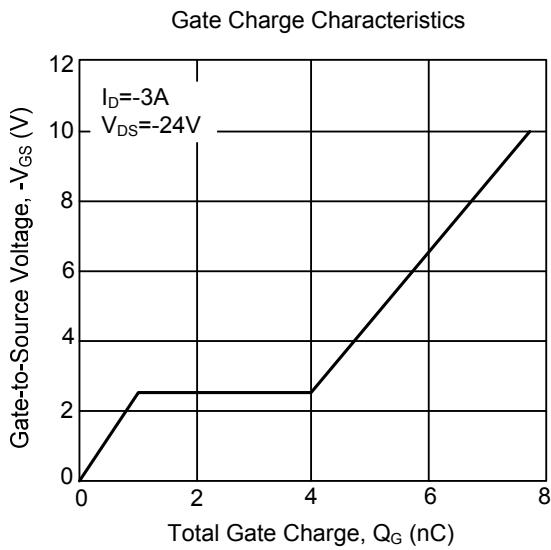
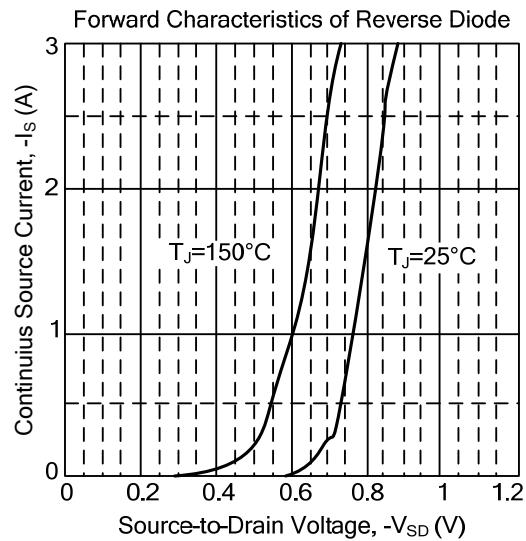
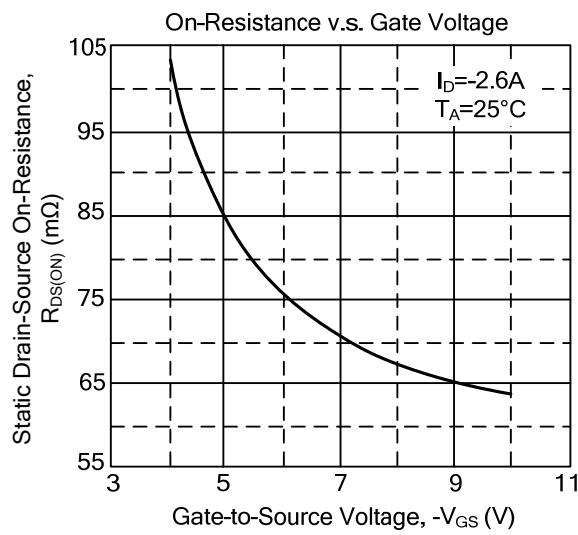
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0\text{ V}, I_D=-250\text{ }\mu\text{A}$	-30			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=-30\text{ V}, V_{GS}=0\text{ V}$			-0.5	$\mu\text{A}$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20\text{ V}, V_{DS}=0\text{ V}$			100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to $25^\circ C$ , $I_D=-1\text{ mA}$	-0.02			$\text{V}/^\circ C$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$	-1		-3	V
Static Drain-Source On-Resistance (Note 2)	$R_{DS(ON)}$	$V_{GS}=-10\text{ V}, I_D=3\text{ A}$			75	$\text{m}\Omega$
		$V_{GS}=-4.5\text{ V}, I_D=2.6\text{ A}$			120	$\text{m}\Omega$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ISS}$	$V_{GS}=0\text{ V}, V_{DS}=-25\text{ V}, f=1.0\text{ MHz}$		412	660	pF
Output Capacitance	$C_{OSS}$			91		pF
Reverse Transfer Capacitance	$C_{RSS}$			62		pF
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge (Note 2)	$Q_G$	$V_{DS}=-24\text{ V}, V_{GS}=-4.5\text{ V}, I_D=-3\text{ A}$		5	8	nC
Gate-Source Charge	$Q_{GS}$			1		nC
Gate-Drain Charge	$Q_{GD}$			3		nC
Turn-ON Delay Time (Note 2)	$t_{D(ON)}$	$V_{DS}=-15\text{ V}, I_D=-1\text{ A}, R_G=3.3\Omega, V_{GS}=-10\text{ V}, R_D=15\Omega$		8		ns
Turn-ON Rise Time	$t_R$			5		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			20		ns
Turn-OFF Fall Time	$t_F$			7		ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Forward On Voltage	$V_{SD}$	$I_S=-1\text{ A}, V_{GS}=0\text{ V}$		-0.76	-1.2	V
Reverse Recovery Time	$t_{RR}$	$I_S=-3\text{ A}, V_{GS}=0\text{ V}, dI/dt=-100\text{ A}/\mu\text{s}$		20		ns
Reverse Recovery Charge	$Q_{RR}$			15		nC

Notes: 1. Pulse width limited by  $T_{J(\text{MAX})}$

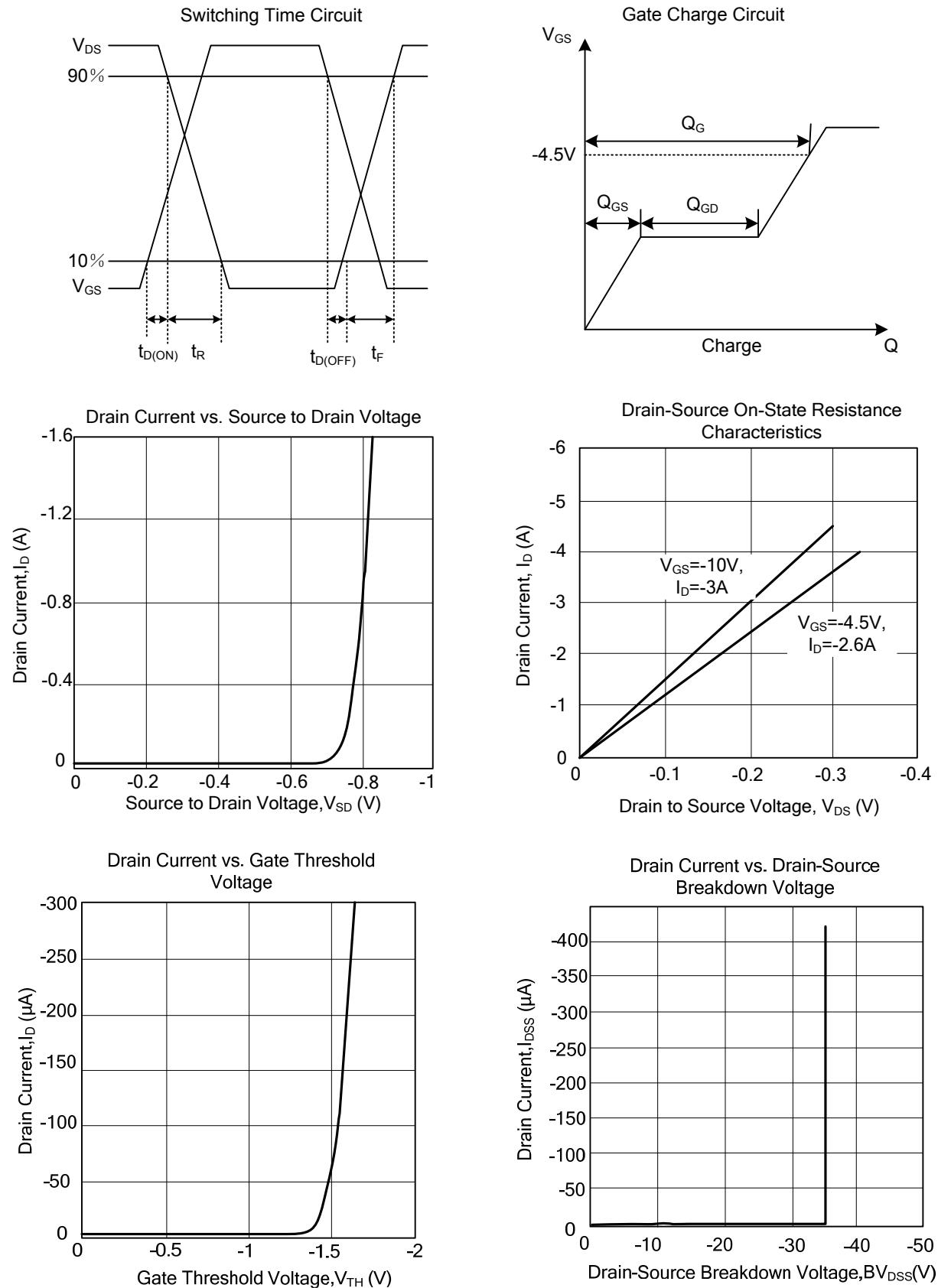
2. Pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

3. Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board.

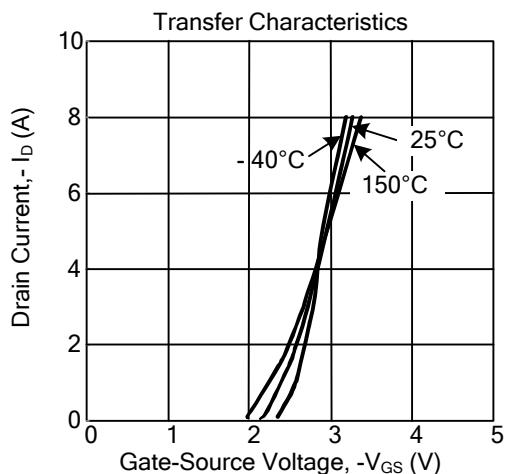
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



## ■ TYPICAL CHARACTERISTICS (Cont.)



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